

EUVL MASK STRUCTURE AND METHOD OF FORMATION

Abstract of the Disclosure

An extreme ultraviolet lithography (EUVL) mask structure and associated method of formation. A first conductive layer is provided between a buffer layer and an absorber layer such that the buffer layer is on a multilayer stack. The multilayer stack is adapted to substantially reflect EUV radiation incident thereon. The absorber layer is adapted to absorb essentially all of EUV radiation incident thereon. A mask pattern is formed in the absorber layer. Formation of the mask pattern in the absorber layer is accompanied by inadvertent formation of a defect in the absorber layer. The defect is subsequently repaired. The mask pattern may be extended into the first conductive layer and into the buffer layer in a substantially defect-free process that exposes a portion of the multilayer stack. A second conductive layer may be provided on the absorber layer, wherein the mask pattern is also formed in the second conductive layer.

Figures